1. Scope :

This specification applies to high speed photodiode chips,
Device No. PD-1240.

2. Structure :

2-1. Planar type : PN Diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Top side (Cathode) : Aluminum alloy

3. Size :

3-1. Chip size : 40 mils × 40 mils (1.016 mm × 1.016 mm).
3-2. Chip thickness : 12 ± 1.5 mils (0.305 ± 0.038 mm).
3-3. Active area : 32 mils × 32 mils (0.813 mm × 0.813 mm).
3-4. Bonding pad (Anode) : 6.4 mils × 6.4mils (0.162mm × 0.162 mm) .
(Cathode) : 6 mils × 6 mils (0.152mm × 0.152mm)
3-5. Pattern drawing : Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark current	I_D	V_R=10V Ee=0mW/cm^2			10	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100 μA Ee=0mW/cm^2	33			V
Open circuit voltage	Voc	T=2856K Ee=5mW/cm^2		410		mV
Short circuit Current	Isc	T=2856K Ee=5mW/cm^2		7		μA
Reverse light current	I_L	V_R =5V T=2856K Ee=5mW/cm^2		7		μA
Total Capacitance	C_T	V_R =5V Ee=0mW/cm^2 f=1MHz		6		pF
Turn-on/ Turn-off Time	ton/toff	V_R=3V R_L=50Ω λ_P=905nm		20/20		nS

※Based on 100% probing